

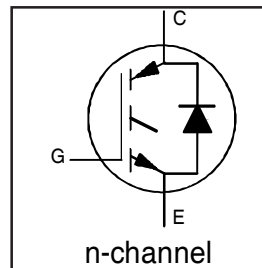
IRG4BC30KD-SPbF

INSULATED GATE BIPOLAR TRANSISTOR WITH ULTRAFAST
SOFT RECOVERY DIODE

Short Circuit Rated
UltraFast IGBT

Features

- High short circuit rating optimized for motor control, $t_{sc} = 10\mu s$, @360V V_{CE} (start), $T_J = 125^\circ C$, $V_{GE} = 15V$
- Combines low conduction losses with high switching speed
- tighter parameter distribution and higher efficiency than previous generations
- IGBT co-packaged with HEXFRED™ ultrafast, ultrasoft recovery antiparallel diodes
- Lead-Free



$V_{CES} = 600V$
 $V_{CE(on)} \text{ typ.} = 2.21V$
@ $V_{GE} = 15V$, $I_C = 16A$

Benefits

- Latest generation 4 IGBTs offer highest power density motor controls possible
- HEXFRED™ diodes optimized for performance with IGBTs. Minimized recovery characteristic reduce noise, EMI and switching losses
- This part replaces the IRGBC30KD2-S and IRGBC30MD2-S products
- For hints see design tip 97003



Absolute Maximum Ratings

	Parameter	Max.	Units
V_{CES}	Collector-to-Emitter Voltage	600	V
$I_C @ T_C = 25^\circ C$	Continuous Collector Current	28	A
$I_C @ T_C = 100^\circ C$	Continuous Collector Current	16	
I_{CM}	Pulsed Collector Current ①	56	
I_{LM}	Clamped Inductive Load Current ②	56	
$I_F @ T_C = 100^\circ C$	Diode Continuous Forward Current	12	
I_{FM}	Diode Maximum Forward Current	58	
t_{sc}	Short Circuit Withstand Time	10	μs
V_{GE}	Gate-to-Emitter Voltage	± 20	V
$P_D @ T_C = 25^\circ C$	Maximum Power Dissipation	100	W
$P_D @ T_C = 100^\circ C$	Maximum Power Dissipation	42	
T_J	Operating Junction and	-55 to +150	$^\circ C$
T_{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 sec.	300 (0.063 in. (1.6mm) from case)	
	Mounting Torque, 6-32 or M3 Screw.	10 lbf•in (1.1 N•m)	

Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case - IGBT	—	1.2	$^\circ C/W$
$R_{\theta JC}$	Junction-to-Case - Diode	—	2.5	
$R_{\theta CS}$	Case-to-Sink, Flat, Greased Surface	0.5	—	
$R_{\theta JA}$	Junction-to-Ambient (PCB Mounted, steady-state) ③	—	40	
Wt	Weight	1.44	—	g

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Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)CES}$	Collector-to-Emitter Breakdown Voltage ^③	600	—	—	V	$V_{GE} = 0V, I_C = 250\mu A$
$\Delta V_{(BR)CES}/\Delta T_J$	Temperature Coeff. of Breakdown Voltage	—	0.54	—	V/ $^\circ\text{C}$	$V_{GE} = 0V, I_C = 1.0mA$
$V_{CE(on)}$	Collector-to-Emitter Saturation Voltage	—	2.21	2.7	V	$I_C = 16A, V_{GE} = 15V$
		—	2.88	—		$I_C = 28A, V_{GE} = 15V$
		—	2.36	—		$I_C = 16A, T_J = 150^\circ\text{C}$
$V_{GE(th)}$	Gate Threshold Voltage	3.0	—	6.0		$V_{CE} = V_{GE}, I_C = 250\mu A$
$\Delta V_{GE(th)}/\Delta T_J$	Temperature Coeff. of Threshold Voltage	—	-12	—	mV/ $^\circ\text{C}$	$V_{CE} = V_{GE}, I_C = 250\mu A$
g_{fe}	Forward Transconductance ^④	5.4	8.1	—	S	$V_{CE} = 100V, I_C = 16A$
I_{CES}	Zero Gate Voltage Collector Current	—	—	250	μA	$V_{GE} = 0V, V_{CE} = 600V$
		—	—	2500		$V_{GE} = 0V, V_{CE} = 600V, T_J = 150^\circ\text{C}$
V_{FM}	Diode Forward Voltage Drop	—	1.4	1.7	V	$I_C = 12A, V_{GE} = 15V$
		—	1.3	1.6		$I_C = 12A, T_J = 150^\circ\text{C}$
I_{GES}	Gate-to-Emitter Leakage Current	—	—	± 100	nA	$V_{GE} = \pm 20V$

Switching Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
Q_g	Total Gate Charge (turn-on)	—	67	100	nC	$I_C = 16A$
Q_{ge}	Gate - Emitter Charge (turn-on)	—	11	16		$V_{CC} = 400V, V_{GE} = 15V$
Q_{gc}	Gate - Collector Charge (turn-on)	—	25	37		See Fig. 8
$t_{d(on)}$	Turn-On Delay Time	—	60	—	ns	$T_J = 25^\circ\text{C}$
t_r	Rise Time	—	42	—		$I_C = 16A, V_{CC} = 480V$
$t_{d(off)}$	Turn-Off Delay Time	—	160	250		$V_{GE} = 15V, R_G = 23\Omega$
t_f	Fall Time	—	80	120	mJ	Energy losses include "tail" and diode reverse recovery
E_{on}	Turn-On Switching Loss	—	0.60	—		See Fig. 9,10,14
E_{off}	Turn-Off Switching Loss	—	0.58	—		
E_{ts}	Total Switching Loss	—	1.18	1.6	μs	$V_{CC} = 360V, T_J = 125^\circ\text{C}$
t_{sc}	Short Circuit Withstand Time	10	—	—		$V_{GE} = 15V, R_G = 10\Omega, V_{CPK} < 500V$
$t_{d(on)}$	Turn-On Delay Time	—	58	—	ns	$T_J = 150^\circ\text{C}, V_{CC} = 480V$
t_r	Rise Time	—	42	—		$I_C = 16A, V_{CC} = 480V$
$t_{d(off)}$	Turn-Off Delay Time	—	210	—		$V_{GE} = 15V, R_G = 23\Omega$
t_f	Fall Time	—	160	—	mJ	Energy losses include "tail" and diode reverse recovery
E_{ts}	Total Switching Loss	—	1.69	—		
L_E	Internal Emitter Inductance	—	7.5	—	nH	Measured 5mm from package
C_{ies}	Input Capacitance	—	920	—	pF	$V_{GE} = 0V$
C_{oes}	Output Capacitance	—	110	—		$V_{CC} = 30V$
C_{res}	Reverse Transfer Capacitance	—	27	—		$f = 1.0MHz$
t_{rr}	Diode Reverse Recovery Time	—	42	60	ns	$T_J = 25^\circ\text{C}$ See Fig. 14
		—	80	120		$T_J = 125^\circ\text{C}$
I_{rr}	Diode Peak Reverse Recovery Current	—	3.5	6.0	A	$T_J = 25^\circ\text{C}$ See Fig. 15
		—	5.6	10		$T_J = 125^\circ\text{C}$
Q_{rr}	Diode Reverse Recovery Charge	—	80	180	nC	$T_J = 25^\circ\text{C}$ See Fig. 16
		—	220	600		$T_J = 125^\circ\text{C}$
$di_{(rec)M}/dt$	Diode Peak Rate of Fall of Recovery During t_b	—	180	—	A/ μs	$T_J = 25^\circ\text{C}$ See Fig. 17

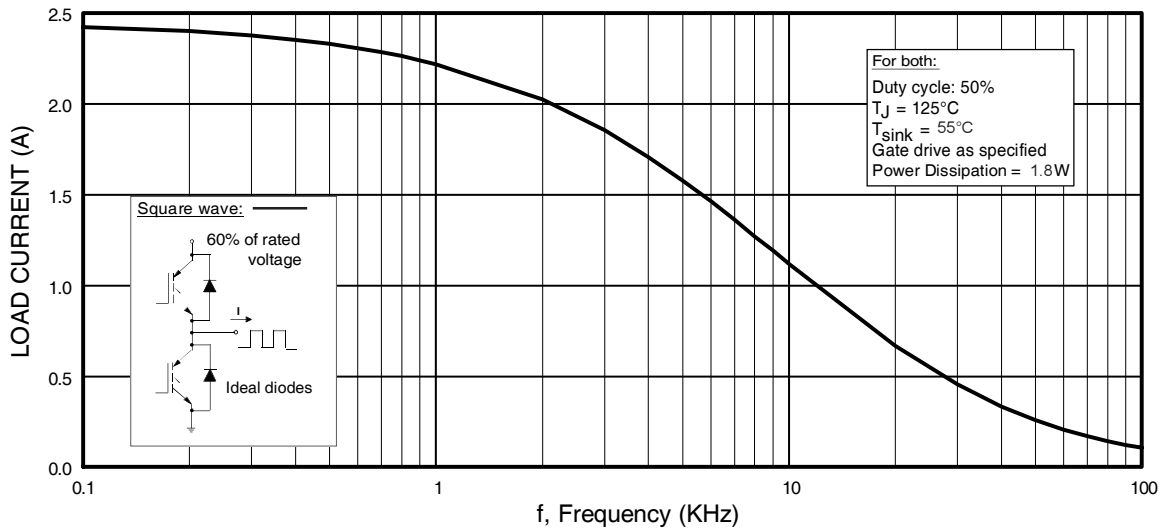


Fig. 1 - Typical Load Current vs. Frequency
(Load Current = I_{RMS} of fundamental)

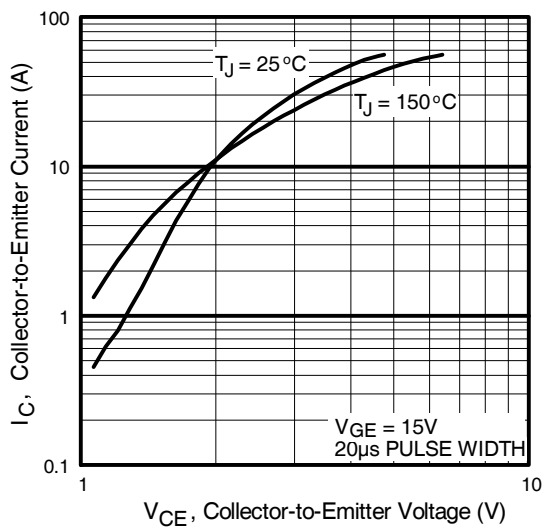


Fig. 2 - Typical Output Characteristics

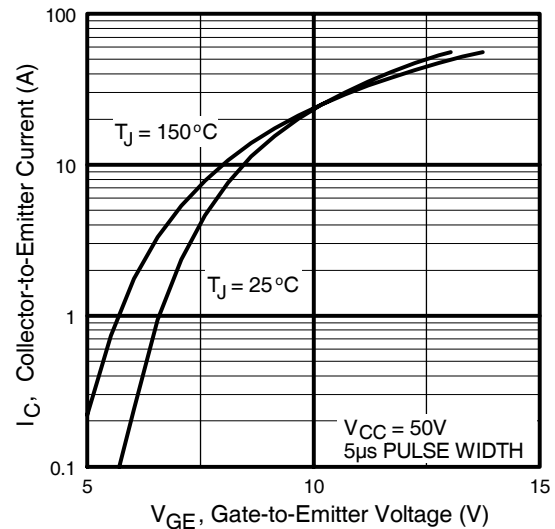


Fig. 3 - Typical Transfer Characteristics

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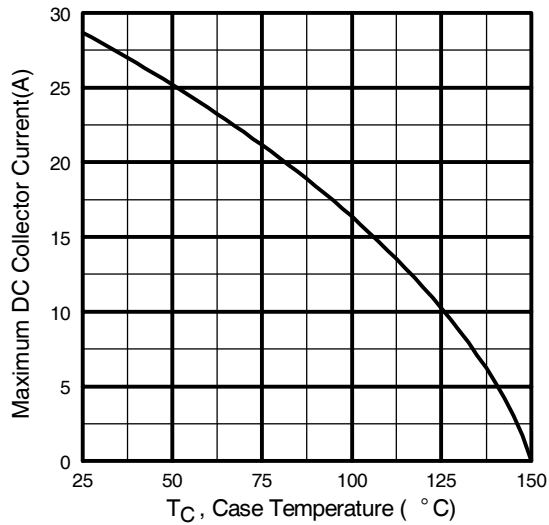


Fig. 4 - Maximum Collector Current vs. Case Temperature

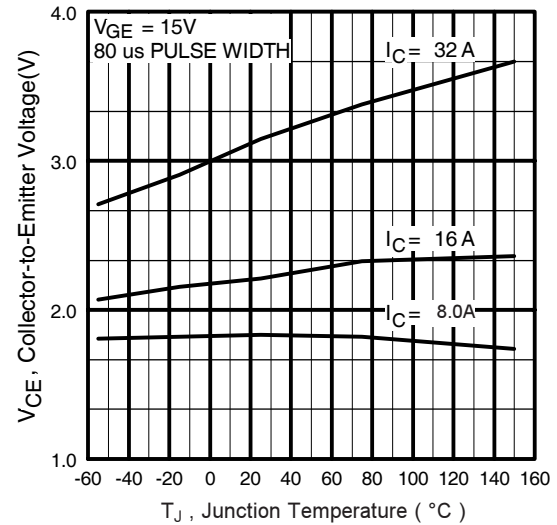


Fig. 5 - Typical Collector-to-Emitter Voltage vs. Junction Temperature

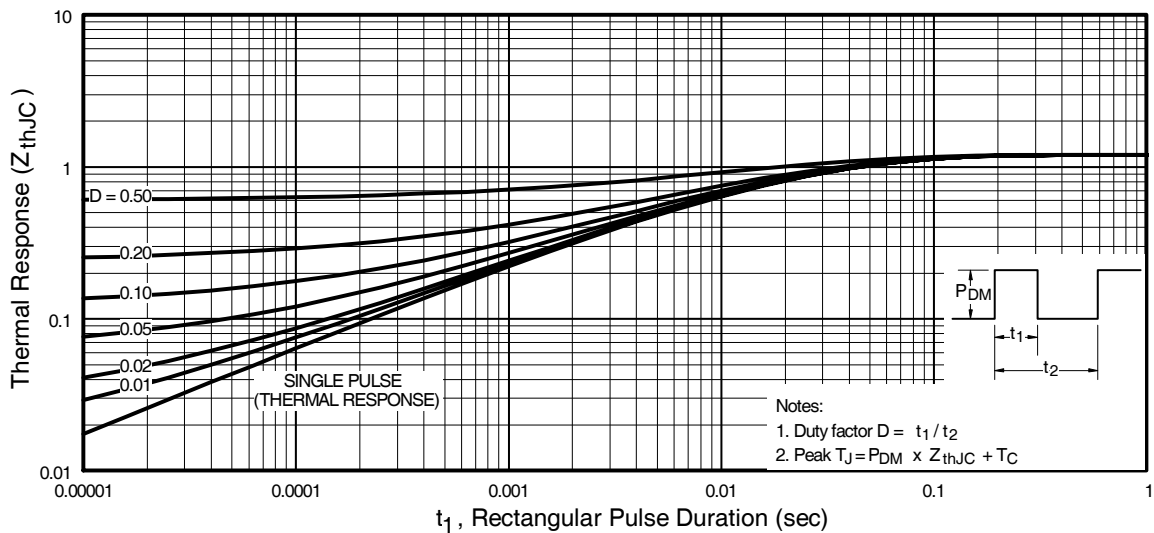


Fig. 6 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

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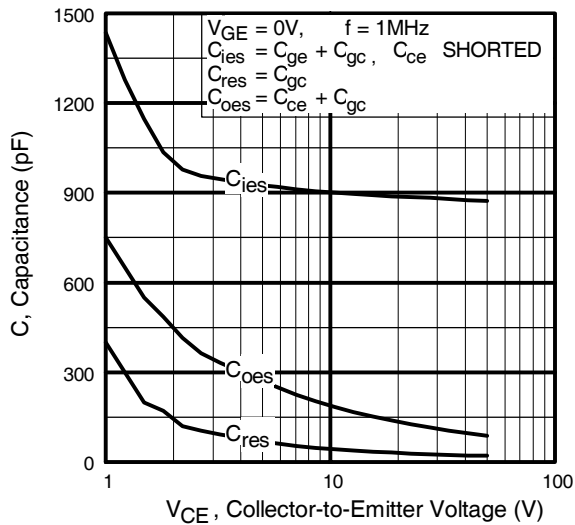


Fig. 7 - Typical Capacitance vs. Collector-to-Emitter Voltage

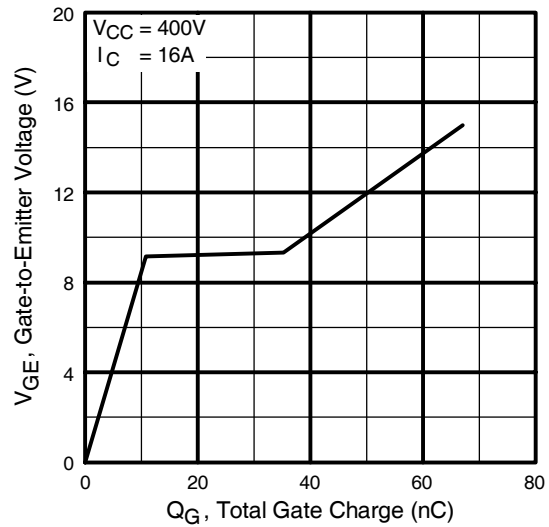


Fig. 8 - Typical Gate Charge vs. Gate-to-Emitter Voltage

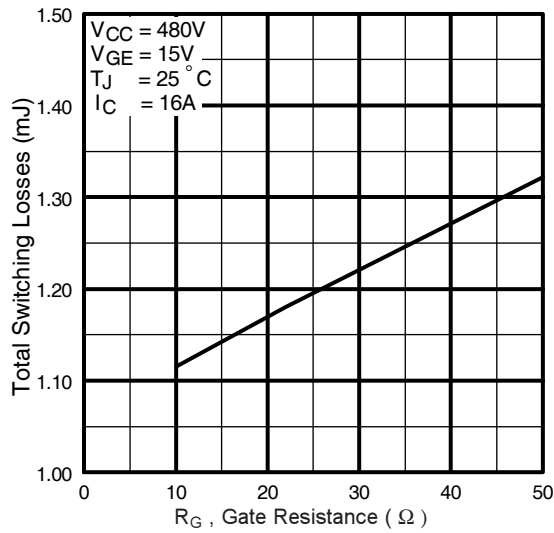


Fig. 9 - Typical Switching Losses vs. Gate Resistance

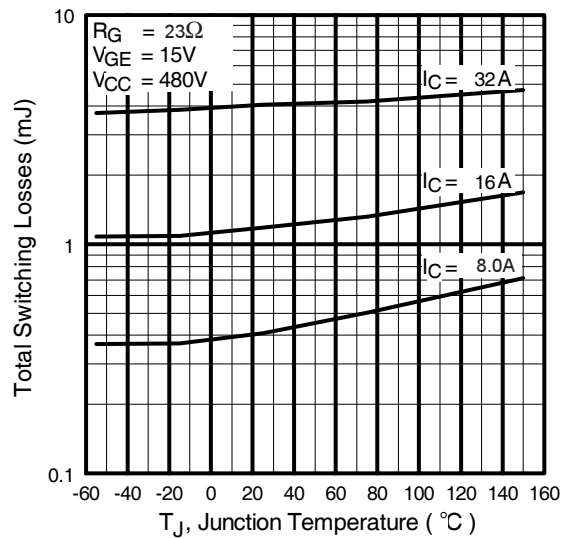
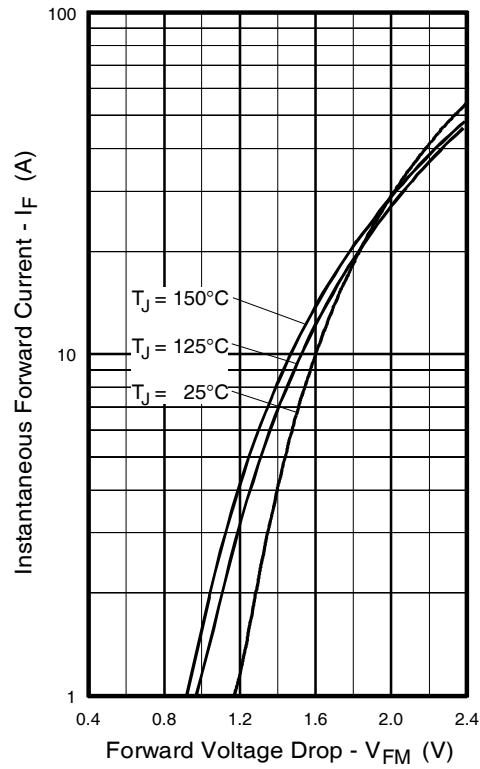
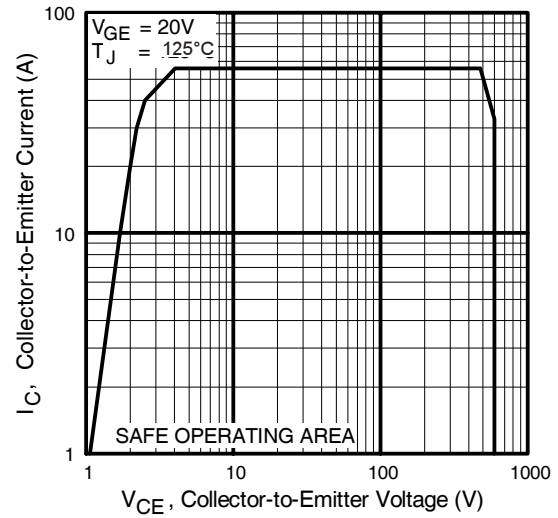
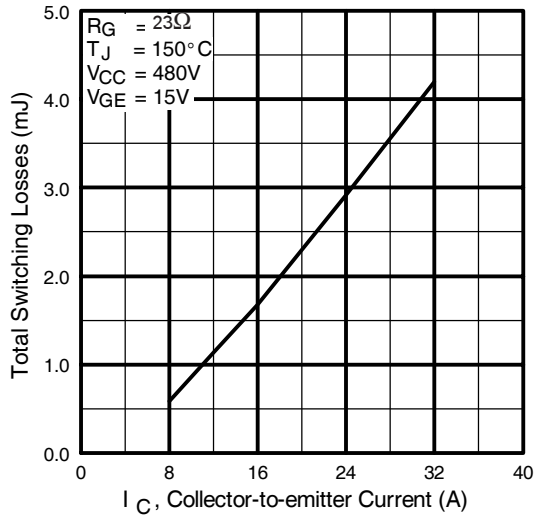


Fig. 10 - Typical Switching Losses vs. Junction Temperature

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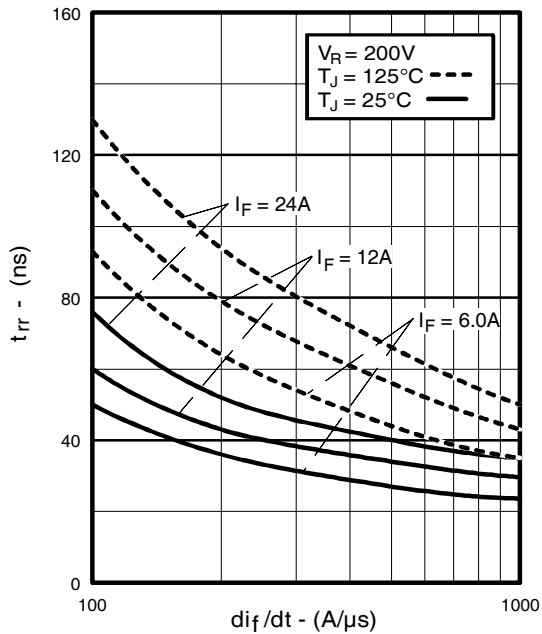


Fig. 14 - Typical Reverse Recovery vs. di_f/dt

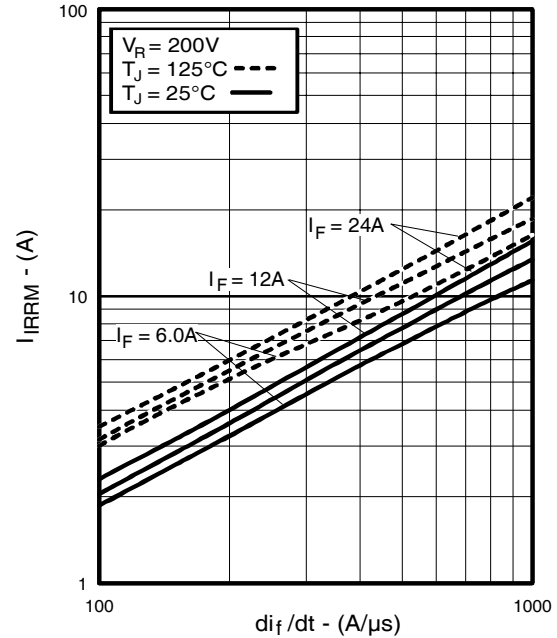


Fig. 15 - Typical Recovery Current vs. di_f/dt

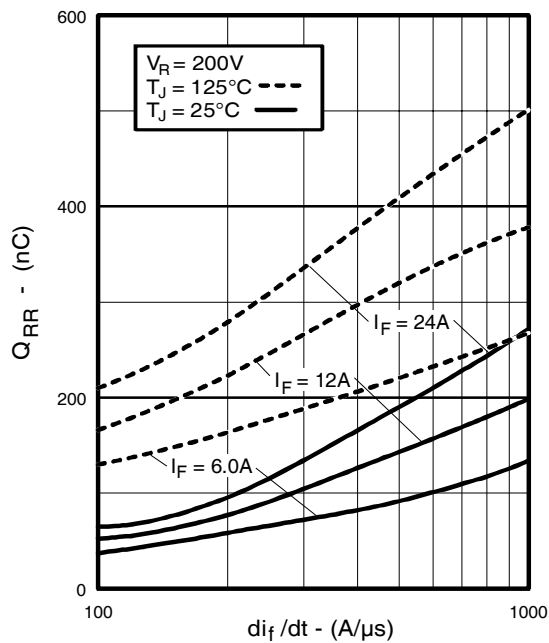


Fig. 16 - Typical Stored Charge vs. di_f/dt

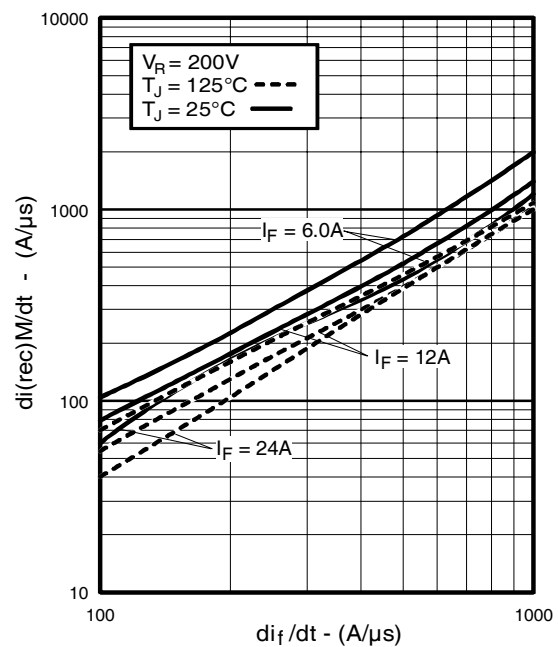


Fig. 17 - Typical $di_{(rec)}M/dt$ vs. di_f/dt

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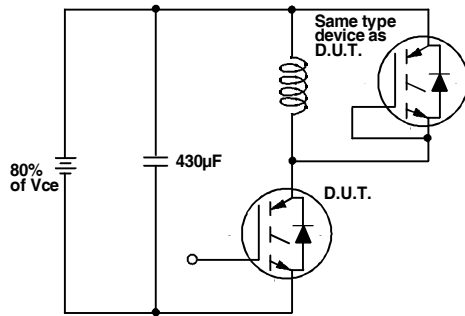


Fig. 18a - Test Circuit for Measurement of I_{LM} , E_{on} , $E_{off}(\text{diode})$, t_{rr} , Q_{rr} , I_{rr} , $t_{d(on)}$, t_r , $t_{d(off)}$, t_f

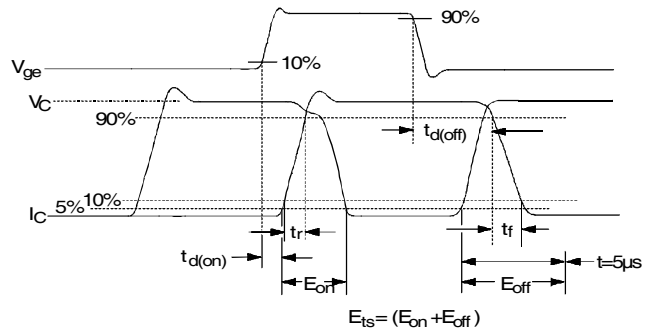


Fig. 18b - Test Waveforms for Circuit of Fig. 18a, Defining E_{off} , $t_{d(off)}$, t_f

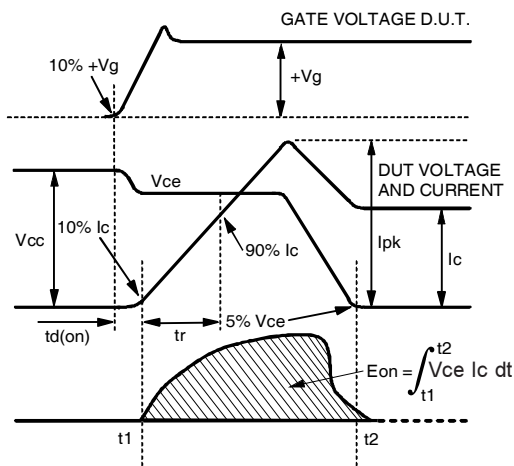


Fig. 18c - Test Waveforms for Circuit of Fig. 18a, Defining E_{on} , $t_{d(on)}$, t_r

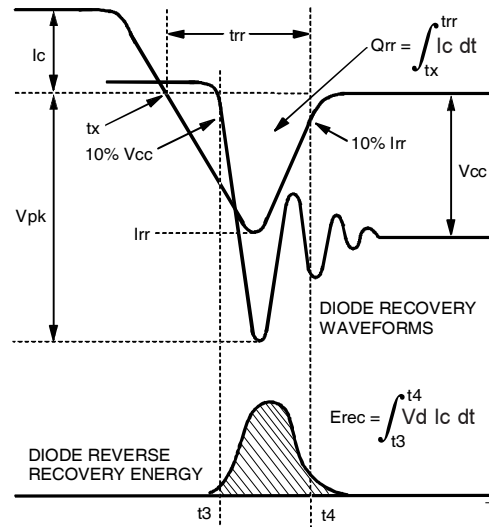


Fig. 18d - Test Waveforms for Circuit of Fig. 18a, Defining E_{rec} , t_{rr} , Q_{rr} , I_{rr}

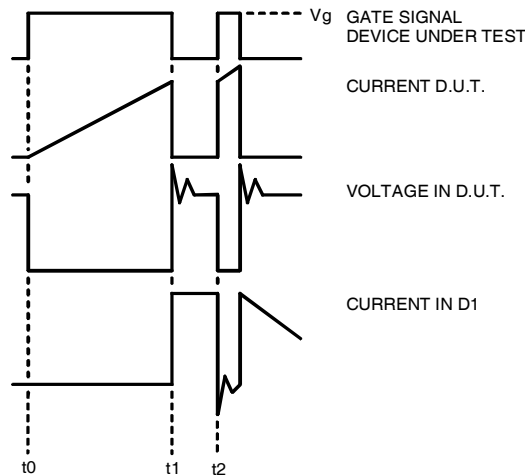


Figure 18e. Macro Waveforms for Figure 18a's Test Circuit

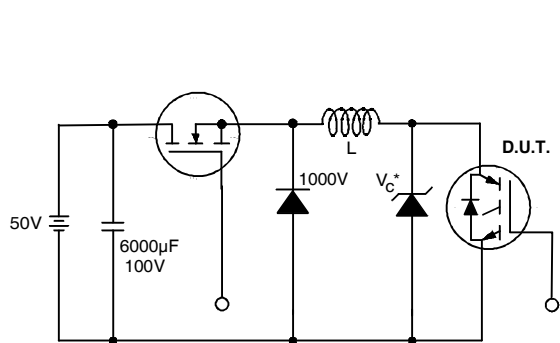


Figure 19. Clamped Inductive Load Test Circuit

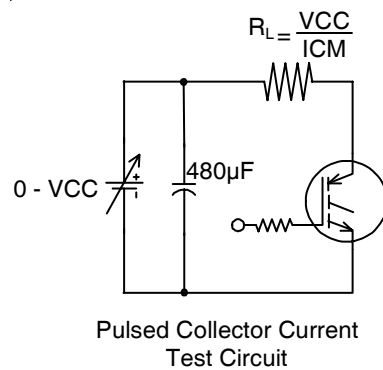


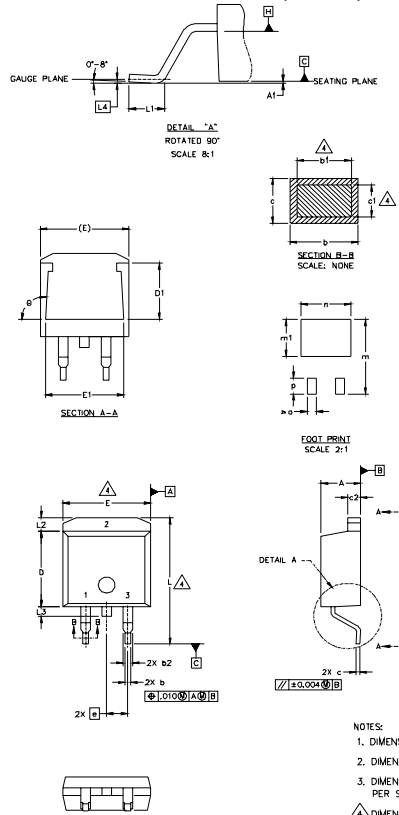
Figure 20. Pulsed Collector Current Test Circuit

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D²Pak Package Outline

Dimensions are shown in millimeters (inches)

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SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	4.06	4.83	.160	.190	4
A1		0.127		.005	
b	0.51	0.99	.020	.039	
b1	0.51	0.89	.020	.035	
b2	1.14	1.40	.045	.055	4
c	0.43	0.63	.017	.025	
c1	0.38	0.74	.015	.029	
c2	1.14	1.40	.045	.055	
D	8.51	9.65	.335	.380	3
D1	5.33		.210		3
E	9.65	10.67	.380	.420	
E1	6.22		.245		
e	2.54 BSC		.100 BSC		
L	14.61	15.88	.575	.625	
L1	1.78	2.79	.070	.110	
L2		1.65		.065	
L3	1.27	1.78	.050	.070	
L4	0.25 BSC		.010 BSC		
m	17.78		.700		
m1	8.89		.350		
n	11.43		.450		
o	2.08		.082		
p	3.81		.150		
θ	90°	93°	90°	93°	

LEAD ASSIGNMENTS

HEXFET

1.- GATE
2.- DRAIN
3.- SOURCE

IGBTs, CoPACK

1.- GATE
2.- COLLECTOR
3.- EMITTER

DIODES

1.- ANODE
2.- CATHODE
3.- ANODE

* PART DEPENDENT.

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994

2. DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).

3. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.127 (.005") PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY.

4. DIMENSION b1 AND c1 APPLY TO BASE METAL ONLY.

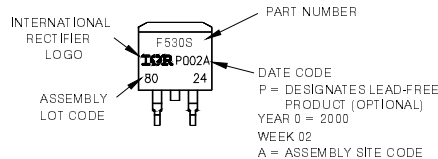
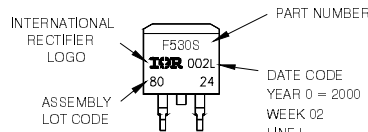
5. CONTROLLING DIMENSION: INCH.

D²Pak Part Marking Information

EXAMPLE: THIS IS AN IRF530S WITH
LOT CODE 8024
ASSEMBLED ON WW 02, 2000
IN THE ASSEMBLY LINE 'L'

Note: 'P' in assembly line
position indicates 'Lead-Free'

OR



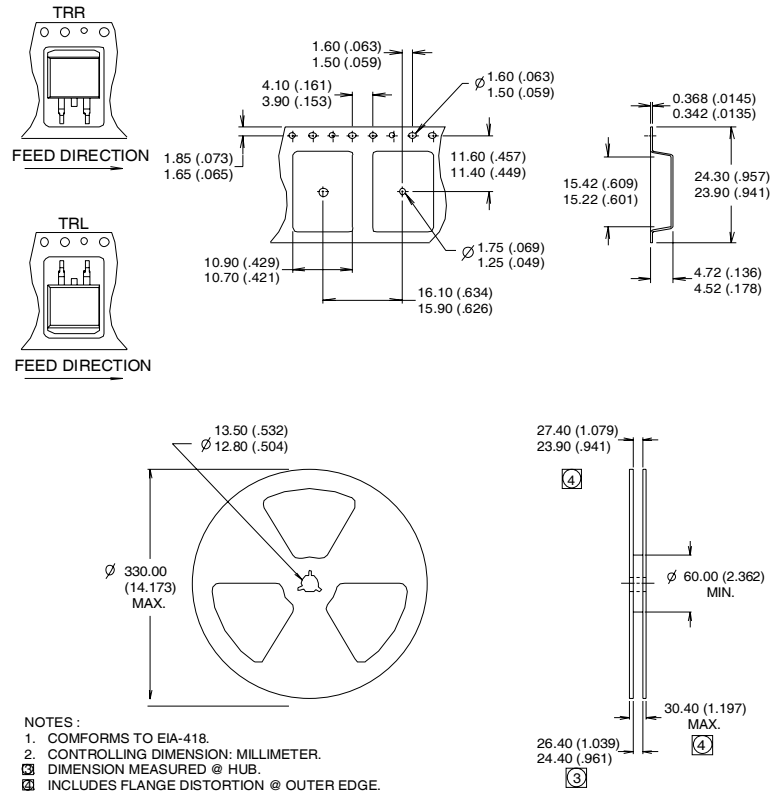
Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

Notes:

- ① Repetitive rating: $V_{GE}=20V$; pulse width limited by maximum junction temperature (figure 20)
- ② $V_{CC}=80\%(V_{CES})$, $V_{GE}=20V$, $L=10\mu H$, $R_G=23\Omega$ (figure 19)
- ③ Pulse width $\leq 80\mu s$; duty factor $\leq 0.1\%$.
- ④ Pulse width $5.0\mu s$, single shot.
- ⑤ When mounted on 1" square PCB (FR-4 or G-10 Material).
For recommended footprint and soldering techniques refer to application note #AN-994.

D²Pak Tape & Reel Information

Dimensions are shown in millimeters (inches)



Data and specifications subject to change without notice.



Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

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